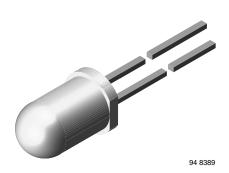
HALOGEN

FREE GREEN

(5-2008)

Vishay Semiconductors

High Speed Infrared Emitting Diode, 830 nm, GaAlAs Double Hetero



DESCRIPTION

TSHG8400 is an infrared, 830 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

Peak wavelength: λ_p = 830 nm

· High reliability

· High radiant power

• High radiant intensity

• Angle of half intensity: $\varphi = \pm 22^{\circ}$

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f_c = 18 MHz

· Good spectral matching with CMOS cameras

 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- · High speed IR data transmission

| PRODUCT SUMMARY | | | | | |
|-----------------|------------------------|---------|---------------------|---------------------|--|
| COMPONENT | I _e (mW/sr) | φ (deg) | λ _p (nm) | t _r (ns) | |
| TSHG8400 | 70 | ± 22 | 830 | 20 | |

Note

• Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | |
|----------------------|-----------|------------------------------|--------------|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | |
| TSHG8400 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | |

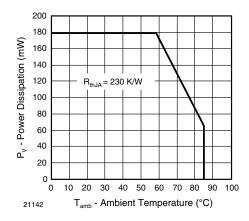
Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified) | | | | | |
|--|--|-------------------|---------------|------|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | |
| Reverse voltage | | V _R | 5 | V | |
| Forward current | | I _F | 100 | mA | |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I _{FM} | 200 | mA | |
| Surge forward current | t _p = 100 μs | I _{FSM} | 1 | Α | |
| Power dissipation | | P _V | 180 | mW | |
| Junction temperature | | Tj | 100 | °C | |
| Operating temperature range | | T _{amb} | - 40 to + 85 | °C | |
| Storage temperature range | | T _{stg} | - 40 to + 100 | °C | |
| Soldering temperature | $t \le 5$ s, 2 mm from case | T _{sd} | 260 | °C | |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm soldered on PCB | R _{thJA} | 230 | K/W | |



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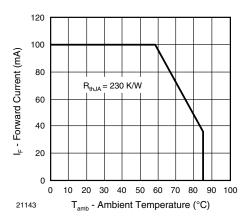


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|---|---|------------------|------|--------|------|-------|
| Forward voltage | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | V _F | | 1.5 | 1.8 | V |
| | $I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$ | V _F | | 2.3 | | V |
| Temperature coefficient of V _F | I _F = 1 mA | TK _{VF} | | - 1.8 | | mV/K |
| Reverse current | V _R = 5 V | I _R | | | 10 | μΑ |
| Junction capacitance | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$ | C _j | | 125 | | pF |
| Radiant intensity | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | l _e | 45 | 70 | 135 | mW/sr |
| | $I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$ | l _e | | 700 | | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | φ _e | | 50 | | mW |
| Temperature coefficient of φ _e | I _F = 100 mA | TKφ _e | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 22 | | deg |
| Peak wavelength | I _F = 100 mA | λ_{p} | | 830 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 40 | | nm |
| Temperature coefficient of λ_p | I _F = 100 mA | TKλ _p | | 0.25 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 20 | | ns |
| Fall time | I _F = 100 mA | t _f | | 13 | | ns |
| Cut-off frequency | I _{DC} = 70 mA, I _{AC} = 30 mA pp | f _c | | 18 | | MHz |
| Virtual source diameter | | d | | 3.7 | | mm |



BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

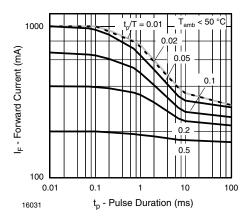


Fig. 3 - Pulse Forward Current vs. Pulse Duration

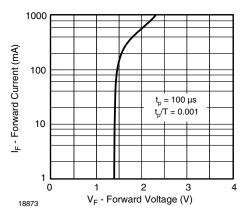


Fig. 4 - Forward Current vs. Forward Voltage

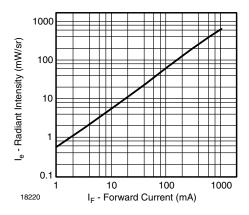


Fig. 5 - Radiant Intensity vs. Forward Current

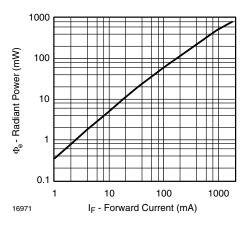


Fig. 6 - Radiant Power vs. Forward Current

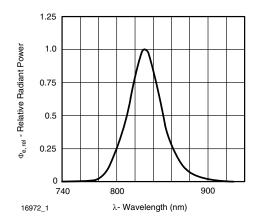


Fig. 7 - Relative Radiant Power vs. Wavelength

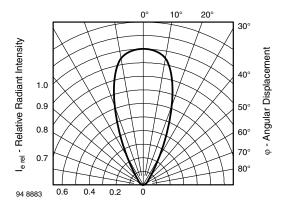
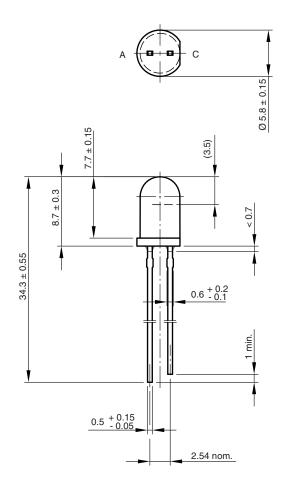
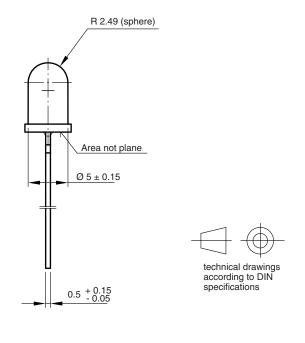


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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PACKAGE DIMENSIONS in millimeters





Drawing-No.: 6.544-5259.06-4 Issue: 6; 19.05.09



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